

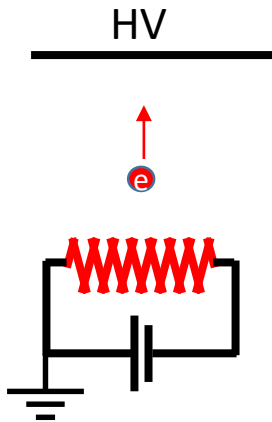
Quantum Tunneling Through a Barrier

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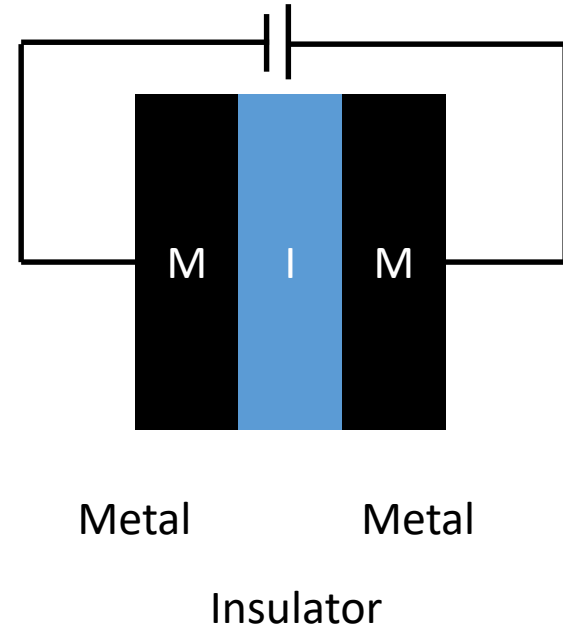
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Example of quantum tunneling of electrons

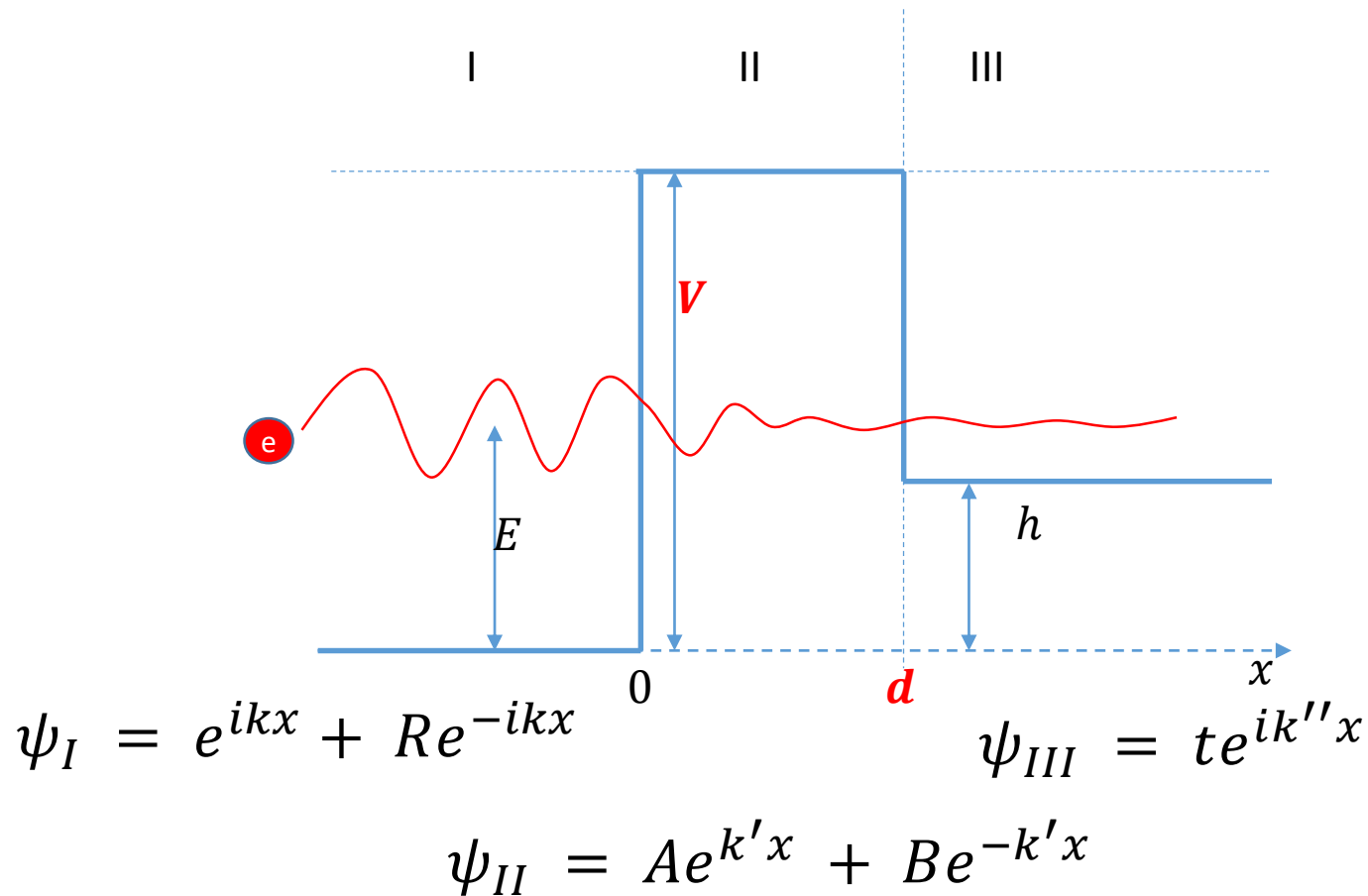
Field emission



Electron transport



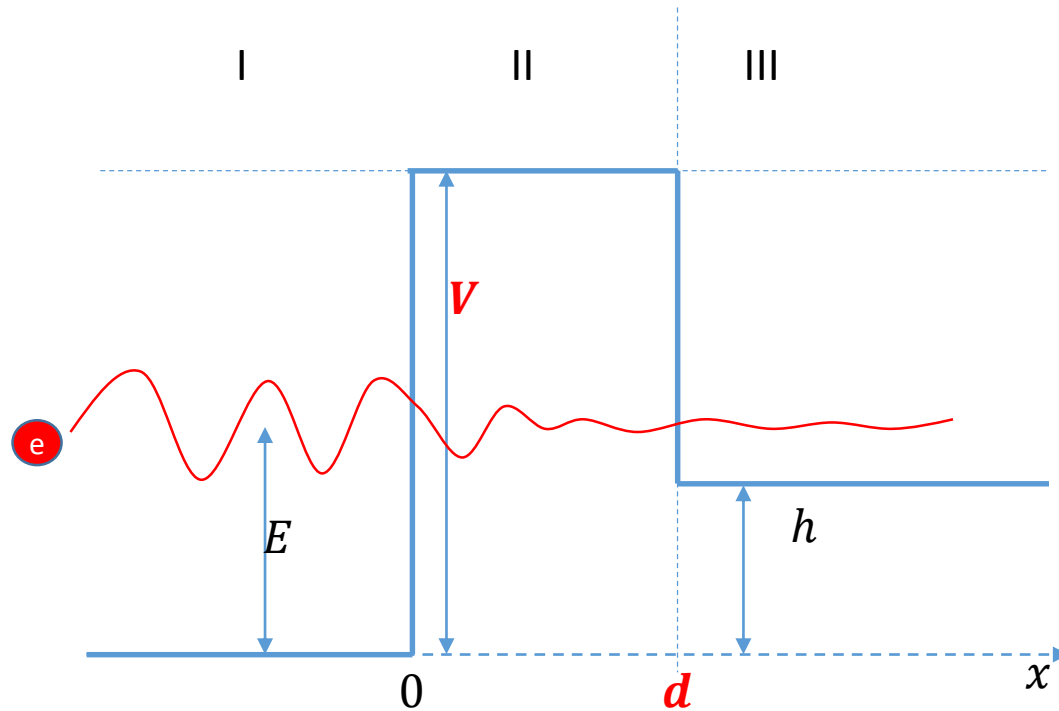
1. Simple model of quantum tunneling



$$k = \sqrt{\frac{2mE}{\hbar^2}}, k' = \sqrt{\frac{2m(V - E)}{\hbar^2}}, k'' = \sqrt{\frac{2m(E - h)}{\hbar^2}}$$

Boundary conditions to solve the problem

$$k = \sqrt{\frac{2mE}{\hbar^2}}, k' = \sqrt{\frac{2m(V - E)}{\hbar^2}}, k'' = \sqrt{\frac{2m(E - h)}{\hbar^2}}$$

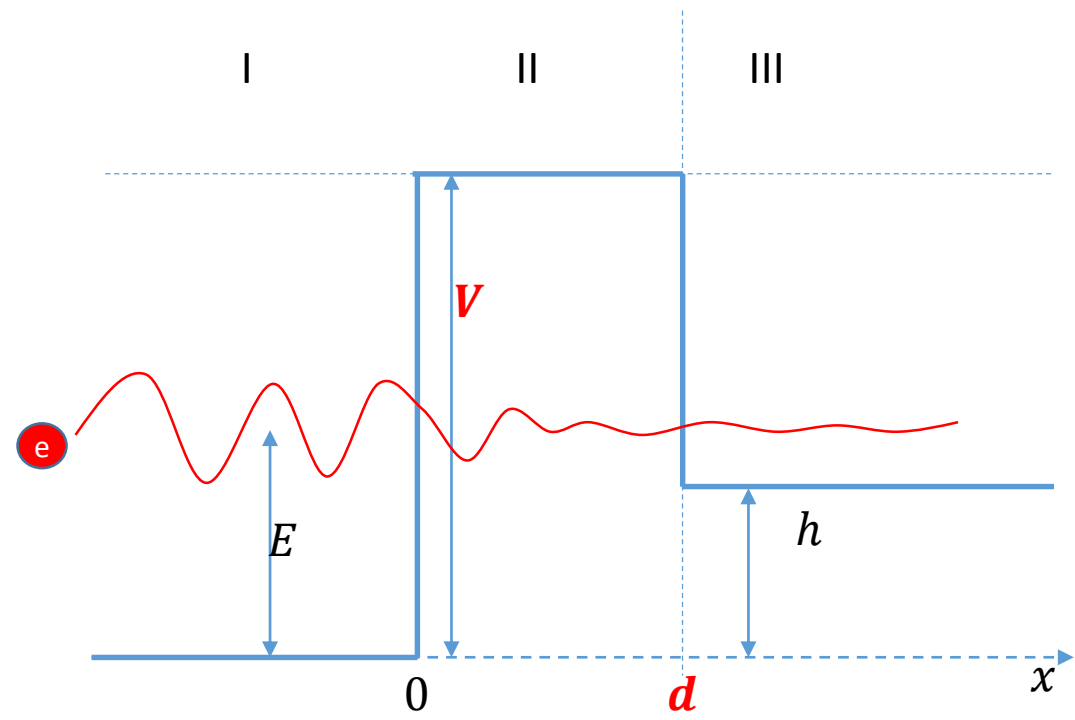


$$\begin{aligned} \psi_I(0) &= \psi_{II}(0) \\ \frac{d\psi_I}{dx} \Big|_{x=0} &= \frac{d\psi_{II}}{dx} \Big|_{x=0} \end{aligned}$$

$$\begin{aligned} \psi_{II}(d) &= \psi_{III}(d) \\ \frac{d\psi_{II}}{dx} \Big|_{x=d} &= \frac{d\psi_{III}}{dx} \Big|_{x=d} \end{aligned}$$

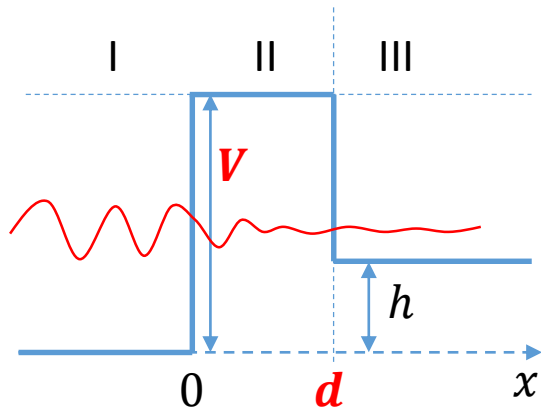
Tunneling probability

$$k = \sqrt{\frac{2mE}{\hbar^2}}, \mathbf{k}' = \sqrt{\frac{2m(\mathbf{V} - E)}{\hbar^2}}, k'' = \sqrt{\frac{2m(E - h)}{\hbar^2}}$$



$$T = |t|^2 = \frac{4(kk')^2}{k'^2(k + k'')^2 \cosh^2(k'd) + (kk'' - k'^2)^2 \sinh^2(k'd)}$$

Tunneling probability



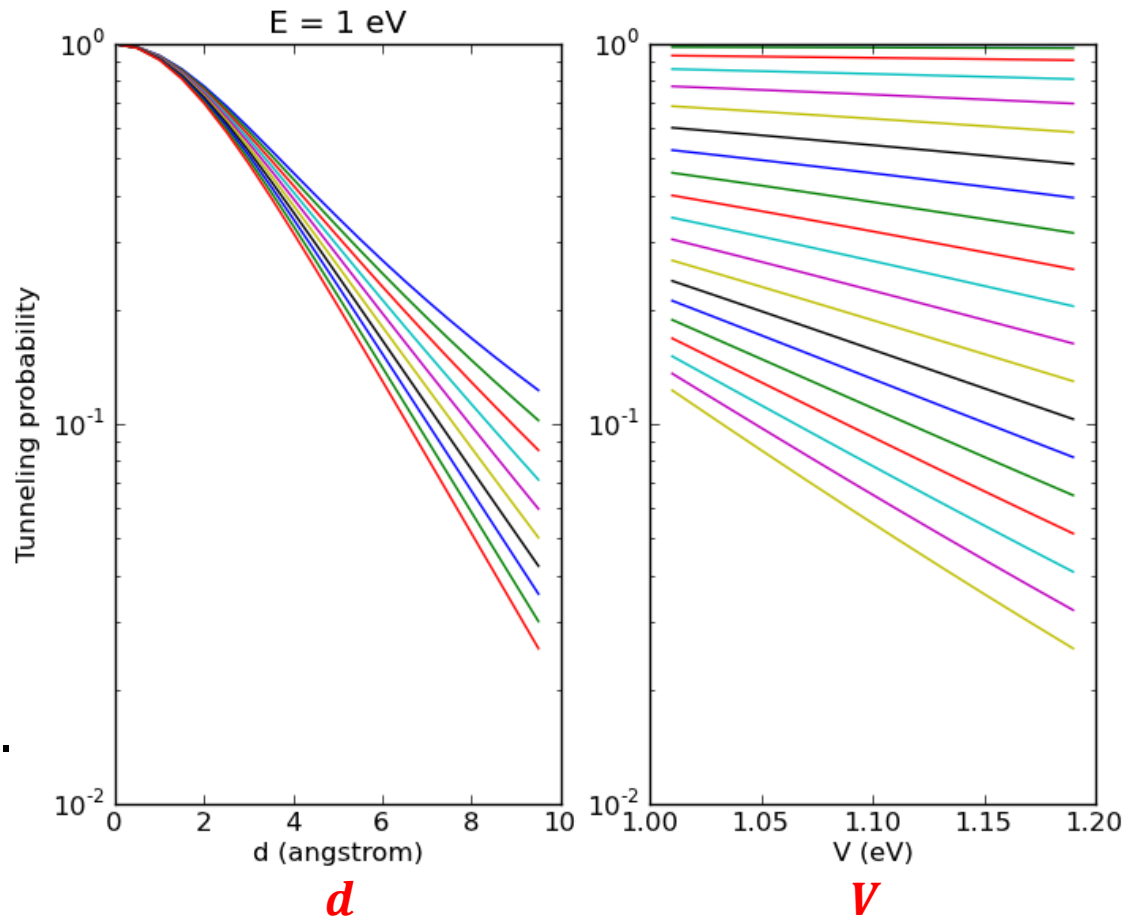
$$k = \sqrt{\frac{2mE}{\hbar^2}}, k' = \sqrt{\frac{2m(V - E)}{\hbar^2}}, k'' = \sqrt{\frac{2m(E - h)}{\hbar^2}}$$

- $k'd \ll 1$
 T

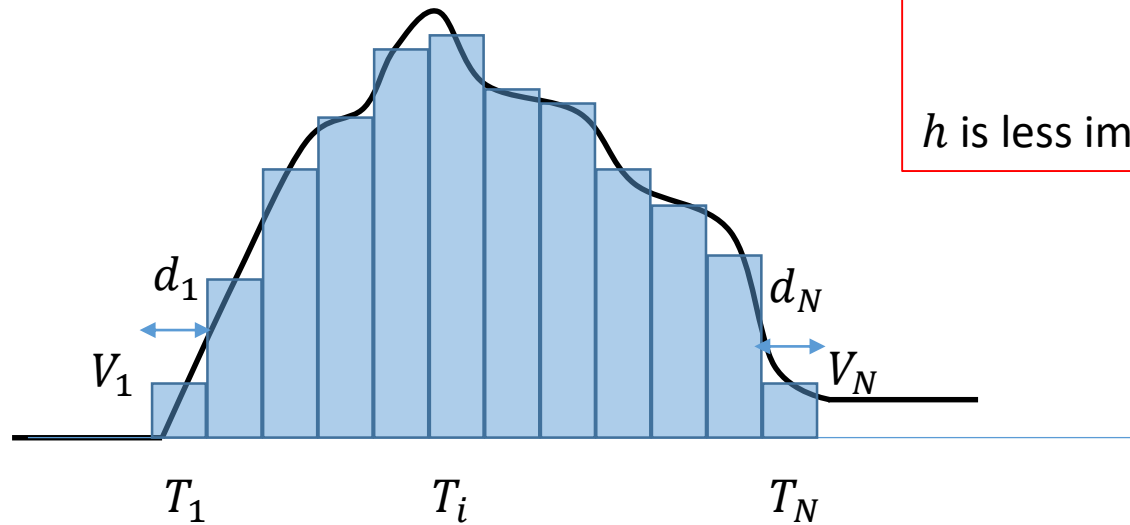
$$= \frac{4k^2}{(k + k'')^2} \left[1 - \frac{(kk'' - k'^2)d^2}{(k + k'')^2} \right]$$

- $k'd \gg 1$

$$T = \frac{4E(V - E)}{V(V - h)} e^{-2k'd}$$



2. Barriers of arbitrary shape



- $k'd \gg 1$

$$T = \frac{4E(V - E)}{V(V - h)} e^{-2k'd}$$

h is less important than the factor $e^{-2k'd}$

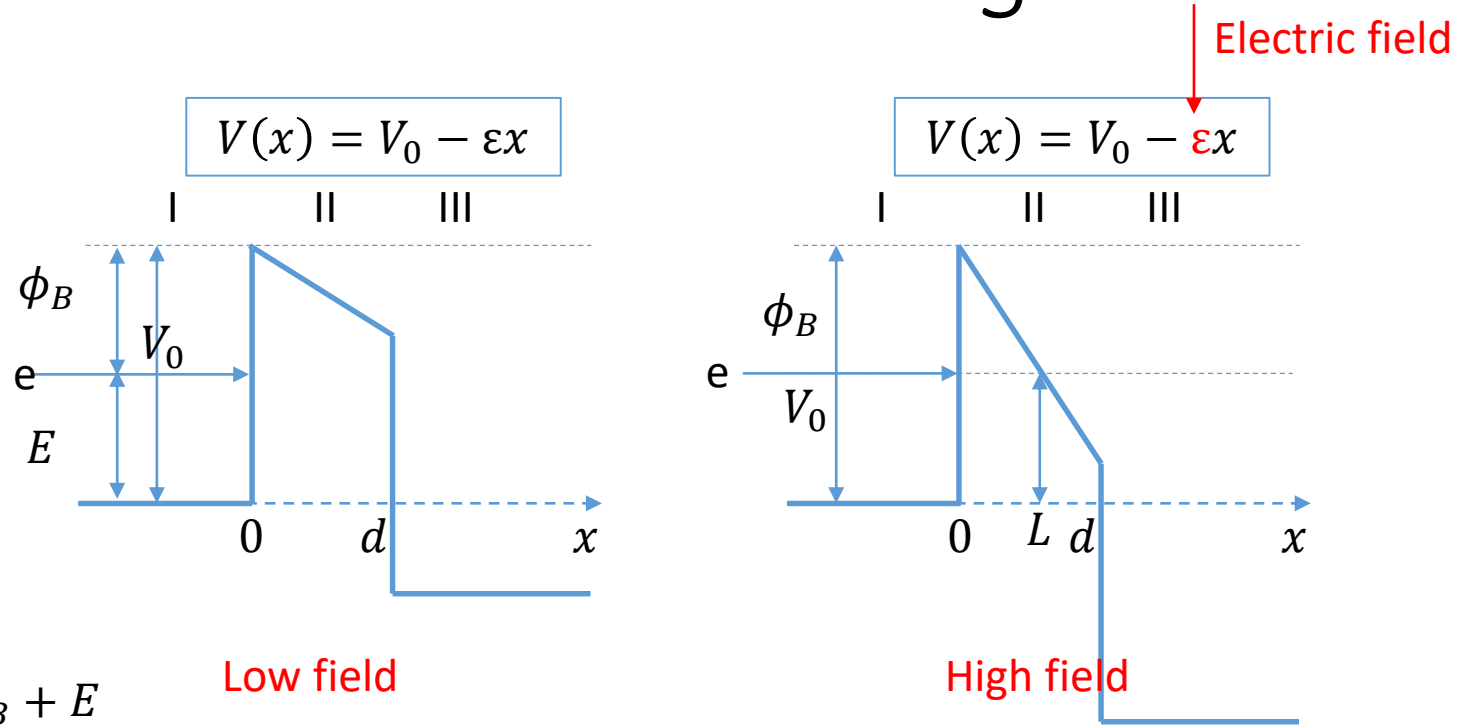
1. Ignore the complexity of h parameter: $T \approx \frac{4E(V - E)}{V^2} e^{-2k'd}$

2. WKB (Wentzel, Kramers, Brillouin) approximation:

$$T = \prod_i T_i = \prod_i \frac{4E(V_i - E)}{V_i^2} e^{-2k'_i d_i} = e^{-2 \sum_i k'_i d_i} \prod_i \frac{4E(V_i - E)}{V_i^2}$$

$$\approx e^{-2 \int k' dx} \prod_i \frac{4E(V_i - E)}{V_i^2}$$

Fowler-Nordheim Tunneling



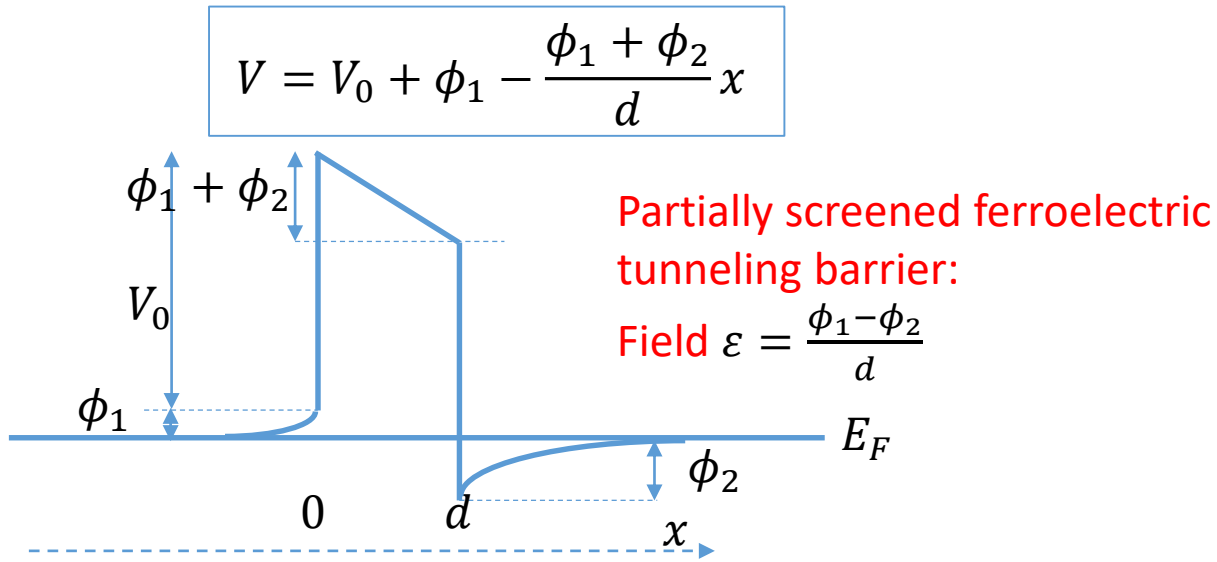
Electric current: $I \propto T \propto e^{-2 \int k' dx} = e^{-\frac{2}{\hbar} \int \sqrt{2m(V-E)} dx}$

$$I \propto e^{-\frac{4\sqrt{2me}}{3\hbar} \frac{[\phi_B^{\frac{3}{2}} - (\phi_B - \epsilon L)^{\frac{3}{2}}]}{\epsilon}}$$

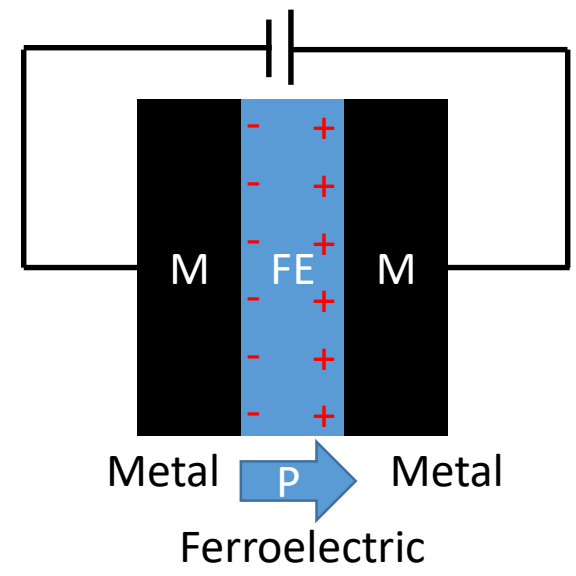
For high field, the tunneling width is L and $\phi_B - \epsilon L = 0$.

$$I \propto e^{-\frac{4\sqrt{2me}}{3\hbar} \frac{\phi_B^{\frac{3}{2}}}{\epsilon}}$$

Tunneling through an asymmetric barrier



Electron transport



- Polarization \rightarrow : $V = V_0 + \phi_1 - \frac{\phi_1 + \phi_2}{d} x$

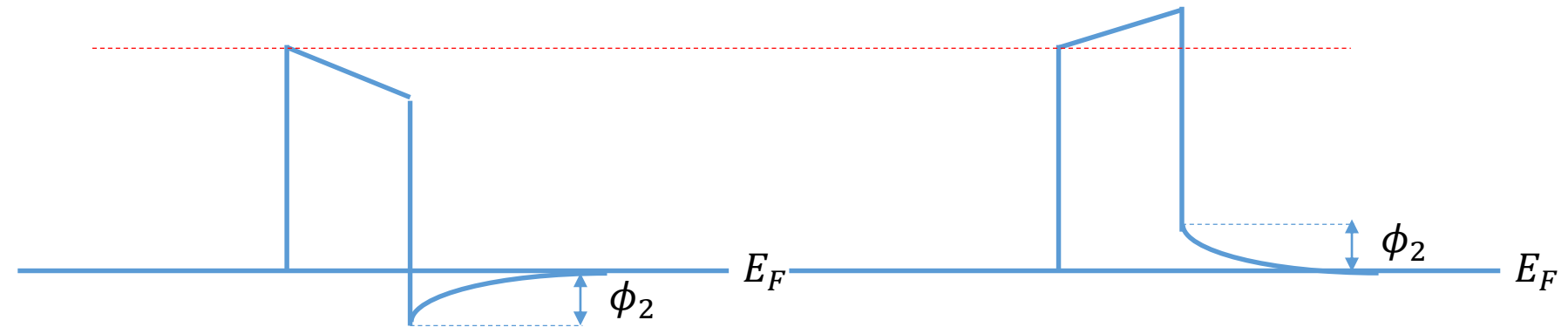
$$I_{\rightarrow} \propto e \frac{4\sqrt{2me}}{3\hbar} \frac{[(V_0 + \phi_1 - E)^{\frac{3}{2}} - (V_0 - \phi_2 - E)^{\frac{3}{2}}]}{\frac{\phi_1 + \phi_2}{d}}$$

- Polarization \leftarrow : $V = V_0 - \phi_1 + \frac{\phi_1 + \phi_2}{d} x$

$$I_{\leftarrow} \propto e \frac{4\sqrt{2me}}{3\hbar} \frac{[(V_0 - \phi_1 - E)^{\frac{3}{2}} - (V_0 + \phi_2 - E)^{\frac{3}{2}}]}{\frac{\phi_2 + \phi_1}{d}}$$

If $\phi_1 \gg \phi_2$,

Tunneling through an asymmetric barrier



Simplified case: $\phi_1 = 0$,

$$I_{\rightarrow} \propto e \frac{4\sqrt{2me}}{3\hbar} \frac{[(V_0 - E)^{\frac{3}{2}} - (V_0 - \phi_2 - E)^{\frac{3}{2}}]}{\frac{\phi_2}{d}}$$

$$I_{\leftarrow} \propto e \frac{4\sqrt{2me}}{3\hbar} \frac{[(V_0 - E)^{\frac{3}{2}} - (V_0 + \phi_2 - E)^{\frac{3}{2}}]}{\frac{\phi_2}{d}}$$

$$I_{\leftarrow} > I_{\rightarrow}$$

It is the over all change of the energy landscape :

$$\int \sqrt{2m(V - E)} dx$$

That caused current difference.

Conclusion

- We used a simple quantum mechanical model to explain the electron tunneling
- The simple model can be used to explain:
 - *Fowler-Nordheim Tunneling*
 - *Tunneling through an asymmetric barrier (ferroelectric barrier)*